



mm inch



#### Lower output capacitance and on resistance. High speed switching. (Turn on time: 0.2ms, Turn off time: 0.08ms).

#### FEATURES

1. Low output capacitance between output terminals and low ONresistance

2. High speed switching (Turn on time: typ. 200 $\mu\text{s})$ 

**3. High sensitivity** Control loads up to 250mA with input current 5mA

**4. Low-level off state leakage current** The SSR has an off state leakage current of several milliamperes, where as this PhotoMOS relay has typ. 20pA even with the rated load voltage

**5. Controls low-level analog signals** PhotoMOS relays features extremely lowclosed-circuit offset voltage to enable control of low-level analog signals without distortion

# 6. Low thermal electromotive force (Approx. 1 $\mu\text{V})$

# RF PhotoMOS (AQV221N)

#### **TYPICAL APPLICATIONS**

Measuring and testing equipment

- 1. Testing equipment for semiconductor performance
- IC tester, Liquid crystal driver tester, semiconductor performance tester 2. Board tester
- Bear board tester, In-circuit tester, function tester
- 3. Medical equipment
- Ultrasonic wave diagnostic machine 4. Multi-point recorder
- (warping, thermo couple)

#### TYPES

Туре	Output rating*			Par	t No.				
			Through hole terminal	Su	rface-mount termi	nal	Packing quantity		
	Load voltage	Load current			Tape and reel packing style				
			Tube pac	king style	Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	Tube	Tape and reel	
AC/DC type	40 V	150 mA	AQV221N	AQV221NA	AQV221NAX	AQV221NAZ	1 tube contains 50 pcs. 1 batch contains 500 pcs.	1,000 pcs.	

\*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

#### RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

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	Item	Symbol	Type of connec- tion	AQV221N(A)	Remarks	
Input	LED forward current	lF		50 mA		
	LED reverse voltage	VR	] \ [	5 V		
	Peak forward current	IFP		1 A	f = 100 Hz, Duty factor = 0.1%	
	Power dissipation	Pin		75 mW		
	Load voltage (peak AC)	V∟		40 V		
	Continuous load current	IL.	Α	0.15 A	A connection: Peak AC, DC B, C connection: DC	
Quitaut			В	0.18 A		
Output			С	0.25 A		
	Peak load current	Ipeak		0.45 A	A connection: 100 ms (1 shot), V <sub>L</sub> = DC	
	Power dissipation	Pout		360 mW		
Total power dissipation		Ρτ		410 mW		
I/O isolation voltage		Viso		1,500 V AC		
Temperature limits	Operating	Topr		-40°C to +85°C -40°F to +185°F	Non-condensing at low temperatures	
	Storage	Tstg		-40°C to +100°C -40°F to +212°F		

#### RF PhotoMOS (AQV221N)

#### 2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item				Symbol	Type of connec- tion**	AQV221N(A)	Remarks	
	LED operate current		Typical	1-		0.90 mA	IL = Max.	
			Maximum	Fon	_	3.0 mA		
Input	I FD turn off current		Minimum	IFoff		0.4 mA	l∟ = Max.	
input			Typical		_	0.85 mA		
	I ED dropout voltage		Typical	VF		1.25 V (1.14 V at I⊧ = 5 mA)	I⊧ = 50 mA	
			Maximum		_	1.5 V		
	On resistance #		Typical	- Ron	A —	9.8 Ω	I⊧ = 0 mA I∟ = Max. Within 1 s on tim	
			Maximum		A	15 Ω		
			Typical	Ron	В	5 Ω	I⊧ = 5 mA I∟ = Max. Within 1 s on tim	
			Maximum		В	7.5 Ω		
Output			Typical	- Ron	0	2.5 Ω	I⊧ = 5 mA	
ouput			Maximum		с —	3.8 Ω	l∟ = Max. Within 1 s on time	
	Output capacitance #		Typical	Cout		3.9 pF	$I_{F} = 0 \text{ mA}$ $V_{B} = 0V$ $f = 1 \text{ MHz}$	
			Maximum		A	5 pF		
	Off state leakage current		Typical	l laak		20 pA	I⊧ = 0 mA	
			Maximum		_	10 nA	V∟ = Max.	
	Switching speed	Turn on time*	Typical	Ton		0.2 ms	I⊧ = 5 mA	
			Maximum		_	0.5 ms	I∟ = Max.	
		Turn off time*	Typical	Toff		0.08 ms	I⊧ = 5 mA I∟ = Max.	
Transfer characteristics			Maximum		_	0.2 ms		
	I/O capacitance		Typical	Ciso		0.8 pF	f = 1 MHz	
			Maximum			1.5 pF	V <sub>B</sub> = 0 V	
	Initial I/O isolation resistance		Minimum	Riso	—	1,000 MΩ	500 V DC	

Note: Recommendable LED forward current IF = 5mA \*Turn on/Turn off time



# Other types of products than the  $C_{out}$  (typ. 3.9pF) and  $R_{on}$  (A connection typ. 9.8 $\Omega$ ) combinations carried in this catalog are also available. (There is a trade-off between Ron and Cout both cannot be reduced at the same time.)

For more information, please contact our sales of ce in y our area.

#### **REFERENCE DATA**

1. Load current vs. ambient temperature characteristics



2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6; LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



3. Turn on time vs. ambient temperature characteristics

LED current: 5 mA;

Load voltage: Max. (DC); Continuous load current: Max. (DC)



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LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



7. LED dropout voltage vs. ambient temperature characteristics LED current: 5 to 50 mA



10. Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



13. Isolation vs. frequency characteristics (50  $\Omega$  impedance)

Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



5. LED operate current vs. ambient temperature characteristics Load voltage: Max. (DC);

Continuous load current: Max. (DC)



8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



11. Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6; Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature:  $25^{\circ}C$  77°F



14. Insertion loss vs. frequency characteristics (50  $\Omega$  impedance)

Measured portion: between terminals 4 and 6; Ambient temperature: 25°C 77°F



6. LED turn off current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



9. Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 4 and 6; Ambient temperature:  $25^\circ C \ 77^\circ F$ 



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6; Frequency: 1 MHz, 30 mVrms; Ambient temperature: 25°C 77°F



15. On resistance distribution Measured portion: between terminals 4 and 6 Continuous load current: 150mA(DC) Quantity, n=50; Ambient temperature: 25°C 77°F



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18. LED operate current distribution Load voltage: 40V(DC) Continuous load current: 150mA(DC) Quantity, n=50; Ambient temperature: 25°C 77°F 35 30 25 20 15 15 20 15 10 5 0

0.7 0.8 0.9 1 LED operate current, mA 1.1

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